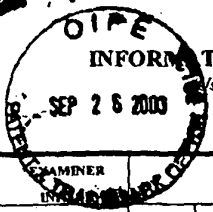


<div style="text-align: center;">  <p>INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)</p> </div>		Docket Number (Optional) SETI-0001	Application Number 09/966563
		Applicant(s) Khan et al.	
Filing Date September 27, 2001		Group Art Unit 2814	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
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EXAMINER LONG PHAM		DATE CONSIDERED 11/1/03	

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.